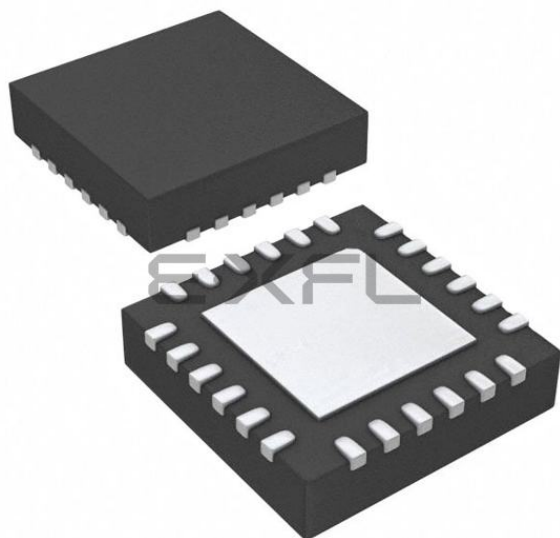




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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	25MHz
Connectivity	I ² C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	17
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 4x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-VQFN Exposed Pad
Supplier Device Package	24-QFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32hg110f32g-a-qfn24r

2.1.21 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.22 General Purpose Input/Output (GPIO)

In the EFM32HG110, there are 17 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 11 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

2.2 Configuration Summary

The features of the EFM32HG110 is a subset of the feature set described in the EFM32HG Reference Manual. Table 2.1 (p. 6) describes device specific implementation of the features.

Table 2.1. Configuration Summary

Module	Configuration	Pin Connections
Cortex-M0+	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO,
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA
CMU	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA
PRS	Full configuration	NA
I2C0	Full configuration	I2C0_SDA, I2C0_SCL
USART0	Full configuration with IrDA and I2S	US0_TX, US0_RX, US0_CLK, US0_CS
USART1	Full configuration with I2S and IrDA	US1_TX, US1_RX, US1_CLK, US1_CS
LEUART0	Full configuration	LEU0_TX, LEU0_RX
TIMER0	Full configuration with DTI	TIM0_CC[2:0], TIM0_CDTI[2:0]
TIMER1	Full configuration	TIM1_CC[2:0]
TIMER2	Full configuration	TIM2_CC[2:0]
RTC	Full configuration	NA
PCNT0	Full configuration, 16-bit count register	PCNT0_S[1:0]
ACMP0	Full configuration	ACMP0_CH[1:0], ACMP0_O
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:6]

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on $T_{AMB}=25^{\circ}\text{C}$ and $V_{DD}=3.0\text{ V}$, as defined in Table 3.2 (p. 8), unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 8), unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 8) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 8).

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150 ¹	$^{\circ}\text{C}$
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	$^{\circ}\text{C}$
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		$V_{DD}+0.3$	V

¹Based on programmed devices tested for 10000 hours at 150°C . Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	$^{\circ}\text{C}$
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			25	MHz
f_{AHB}	Internal AHB clock frequency			25	MHz

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I _{EM1}	EM1 current	24 MHz HFXO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =25°C		64	68	µA/ MHz
		24 MHz HFXO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =85°C		67	71	µA/ MHz
		24 MHz USHFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =25°C		85	91	µA/ MHz
		24 MHz USHFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =85°C		86	92	µA/ MHz
		24 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =25°C		51	55	µA/ MHz
		24 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =85°C		52	56	µA/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =25°C		53	57	µA/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =85°C		54	58	µA/ MHz
		14 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =25°C		56	59	µA/ MHz
		14 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =85°C		57	61	µA/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =25°C		58	61	µA/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =85°C		59	63	µA/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =25°C		64	68	µA/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =85°C		67	71	µA/ MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =25°C		106	114	µA/ MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V _{DD} = 3.0 V, T _{AMB} =85°C		114	126	µA/ MHz
I _{EM2}	EM2 current	EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V _{DD} = 3.0 V, T _{AMB} =25°C		0.9	1.35	µA

Figure 3.3. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 14 MHz

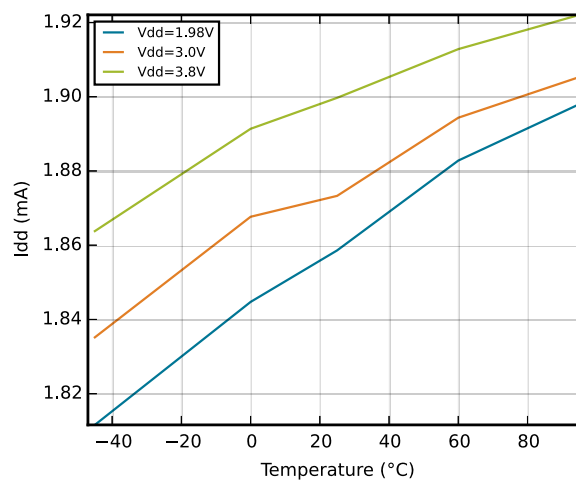
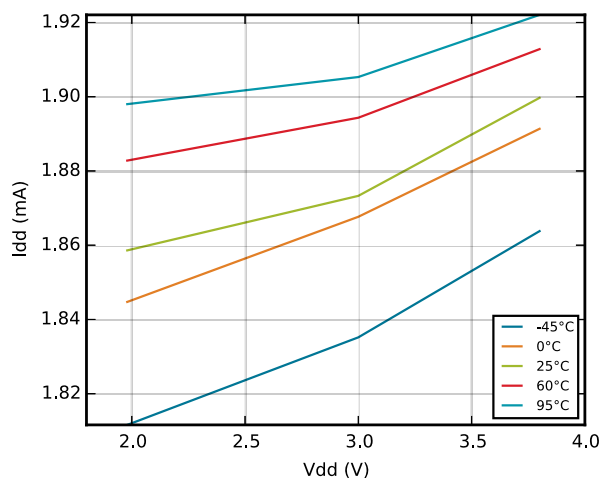


Figure 3.4. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 11 MHz

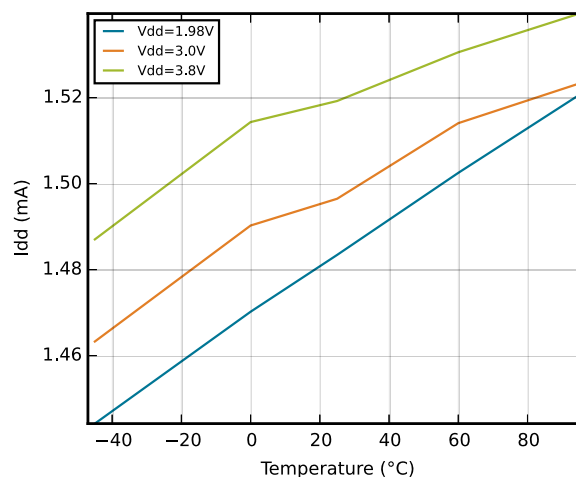
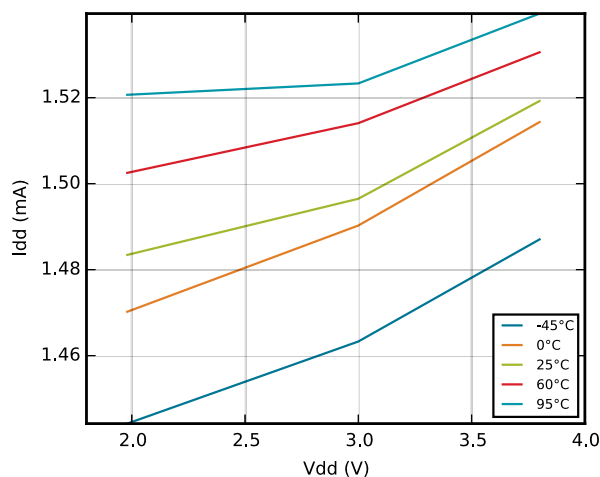


Figure 3.7. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 21 MHz

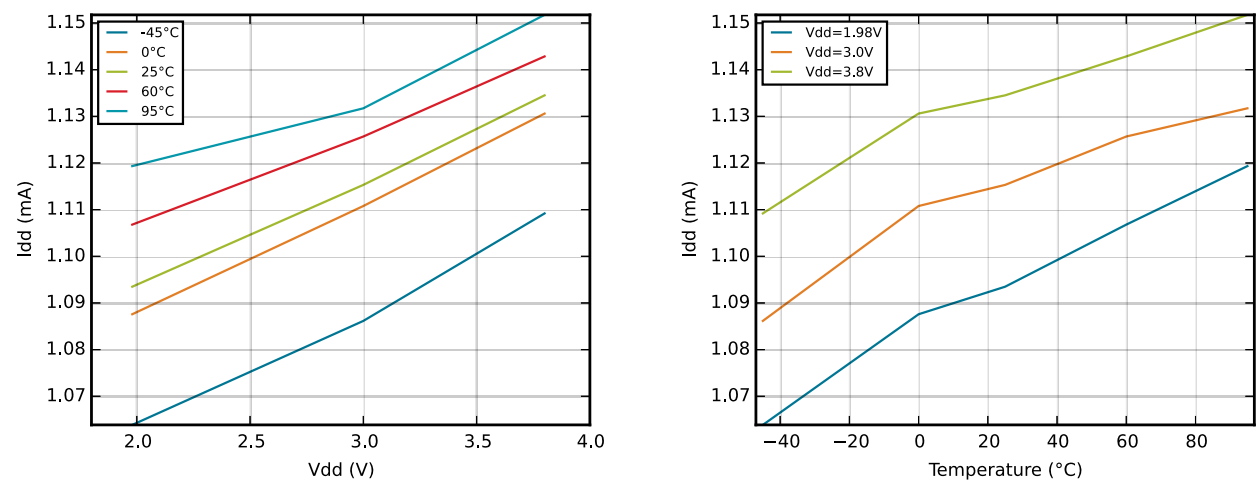


Figure 3.8. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 14 MHz

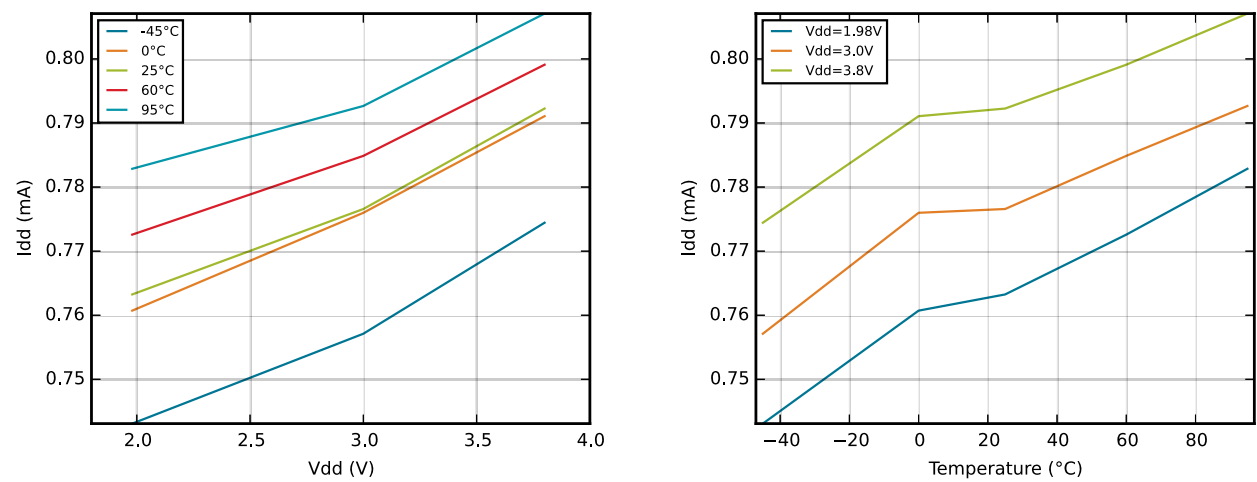


Figure 3.9. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 11 MHz

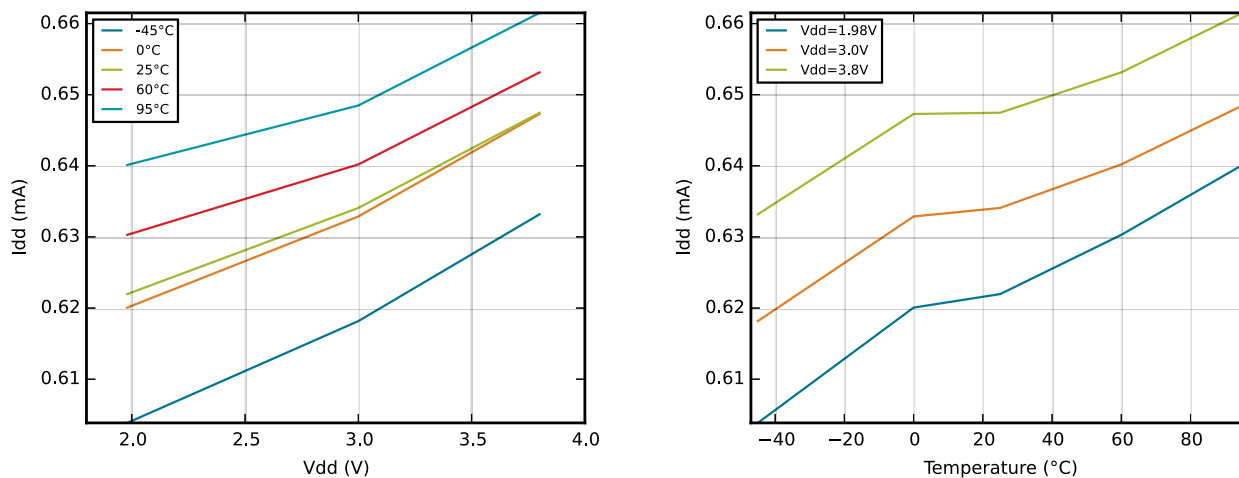
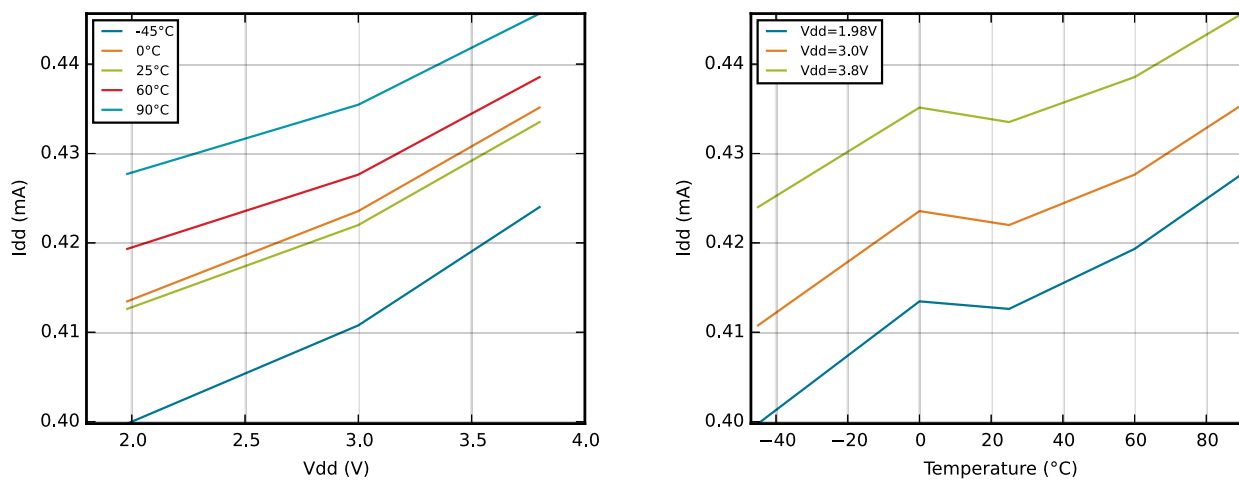
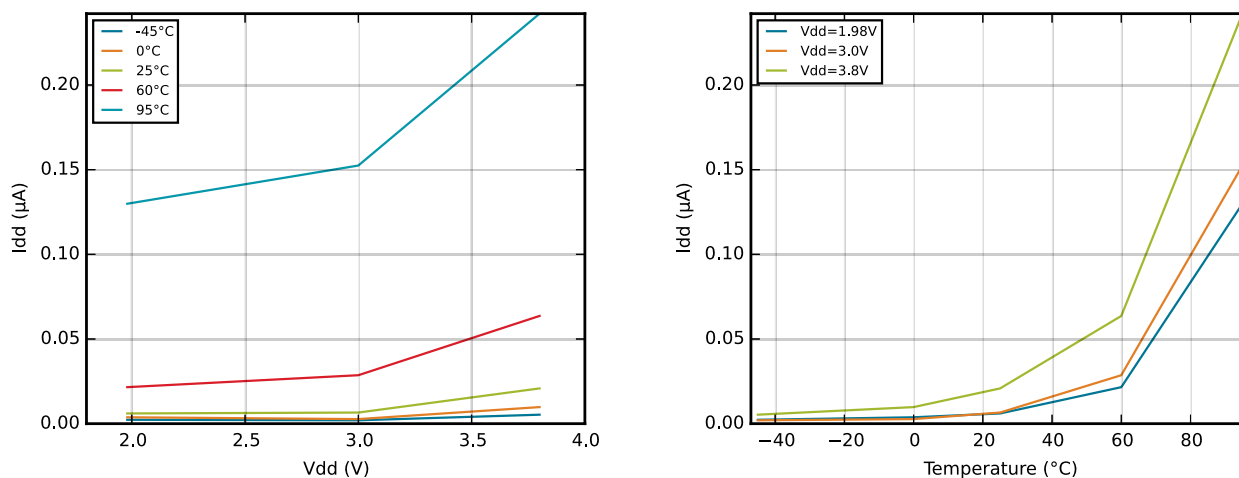


Figure 3.10. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 6.6 MHz



3.4.5 EM4 Current Consumption

Figure 3.13. EM4 current consumption.



3.5 Transition between Energy Modes

The transition times are measured from the trigger to the first clock edge in the CPU.

Table 3.4. Energy Modes Transitions

Symbol	Parameter	Min	Typ	Max	Unit
t_{EM10}	Transition time from EM1 to EM0		0		HF-CORE-CLK cycles
t_{EM20}	Transition time from EM2 to EM0		2		μs
t_{EM30}	Transition time from EM3 to EM0		2		μs
t_{EM40}	Transition time from EM4 to EM0		163		μs

3.6 Power Management

The EFM32HG requires the AVDD_x, VDD_DREG and IOVDD_x pins to be connected together (with optional filter) at the PCB level. For practical schematic recommendations, please see the application note, "AN0002 EFM32 Hardware Design Considerations".

Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{BODextthr-}	BOD threshold on falling external supply voltage	EM0	1.74		1.96	V
		EM2	1.71	1.86	1.98	V
V _{BODextthr+}	BOD threshold on rising external supply voltage			1.85		V
t _{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		μs
C _{DECOUPLE}	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		μF

3.7 Flash

Table 3.6. Flash

Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC _{FLASH}	Flash erase cycles before failure		20000			cycles
RET _{FLASH}	Flash data retention	T _{AMB} <150°C	10000			h
		T _{AMB} <85°C	10			years
		T _{AMB} <70°C	20			years
t _{W_PROG}	Word (32-bit) programming time		20			μs
t _{P_ERASE}	Page erase time		20	20.4	20.8	ms
t _{D_ERASE}	Device erase time		40	40.8	41.6	ms
I _{ERASE}	Erase current				7 ¹	mA
I _{WRITE}	Write current				7 ¹	mA
V _{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

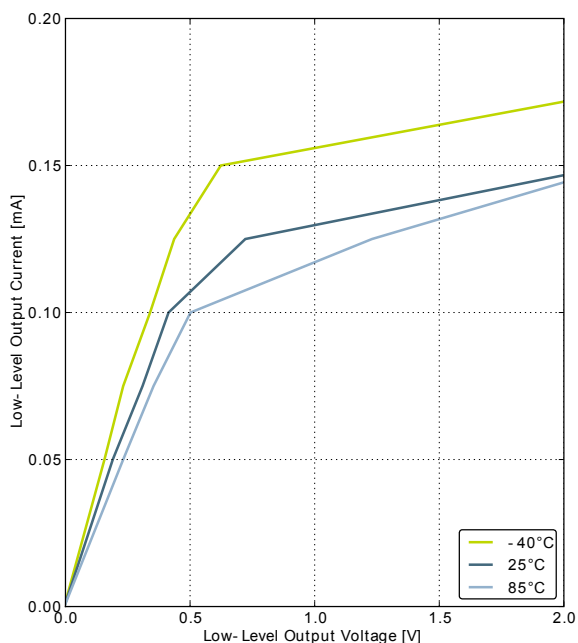
¹Measured at 25°C

3.8 General Purpose Input Output

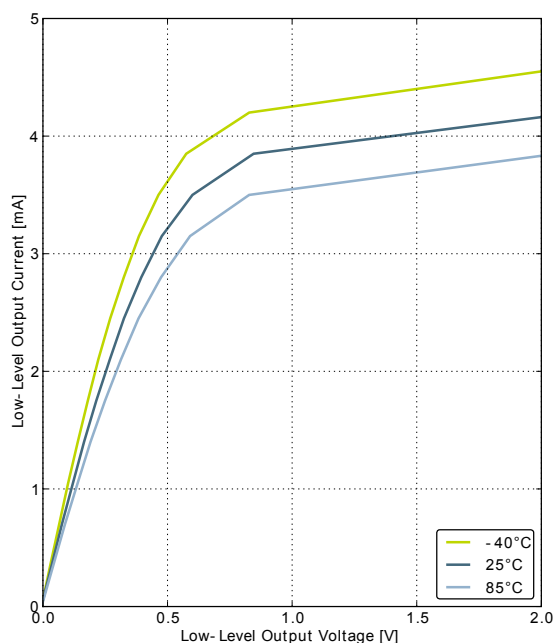
Table 3.7. GPIO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{IOIL}	Input low voltage				0.30V _{DD}	V
V _{IOIH}	Input high voltage		0.70V _{DD}			V
V _{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V _{DD}		V
		Sourcing 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V _{DD}		V

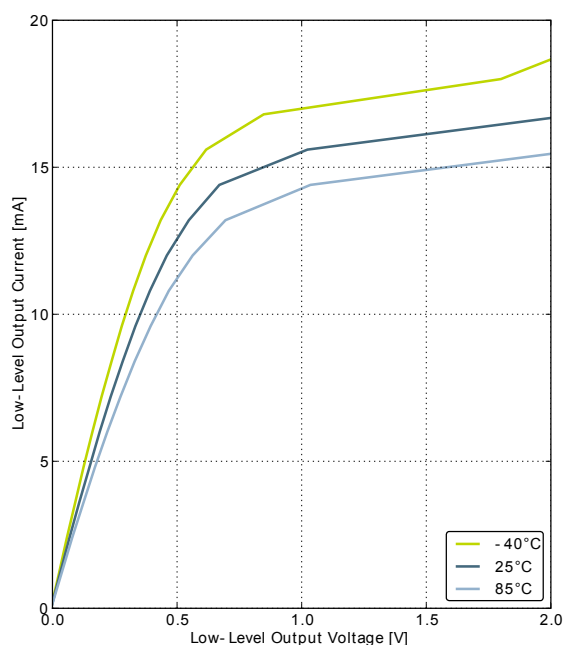
Figure 3.14. Typical Low-Level Output Current, 2V Supply Voltage



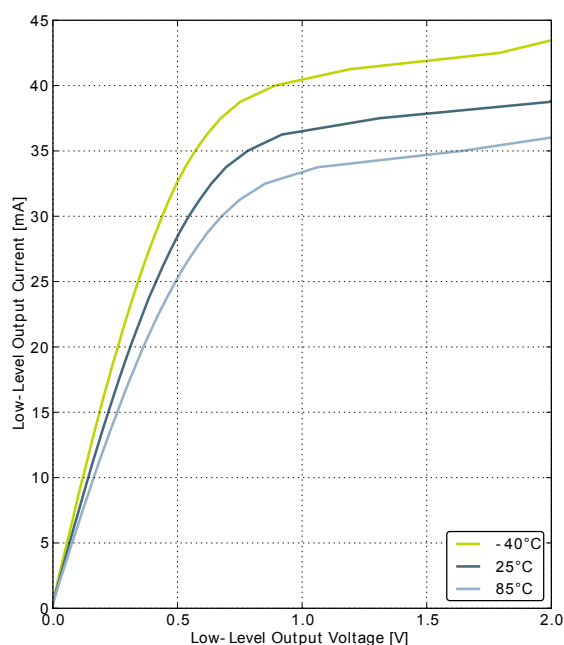
GPIO_Px_CTRL DRIVEMODE = LOWEST



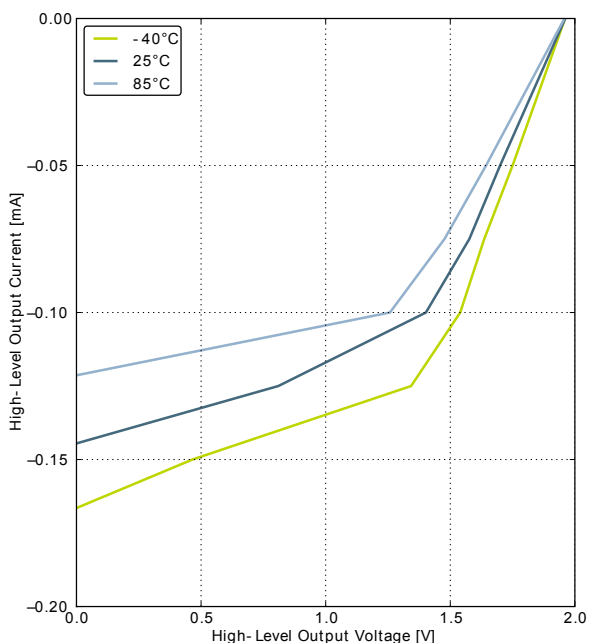
GPIO_Px_CTRL DRIVEMODE = LOW



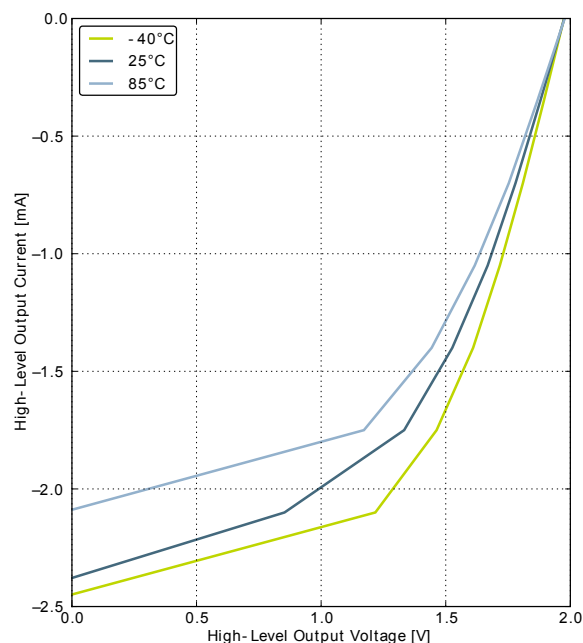
GPIO_Px_CTRL DRIVEMODE = STANDARD



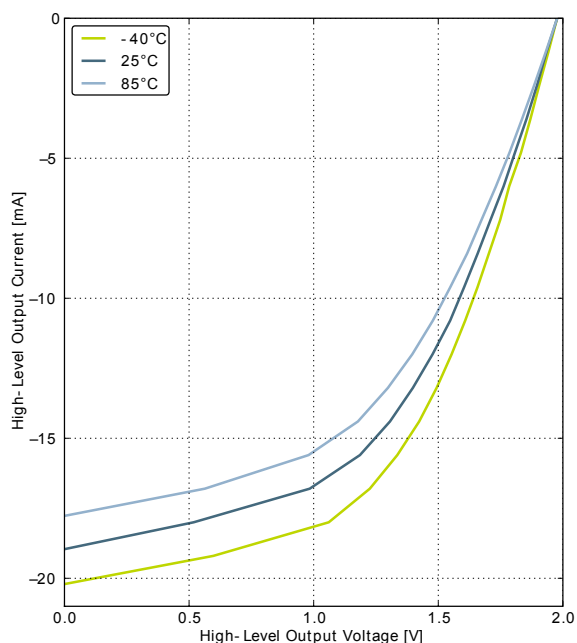
GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.15. Typical High-Level Output Current, 2V Supply Voltage

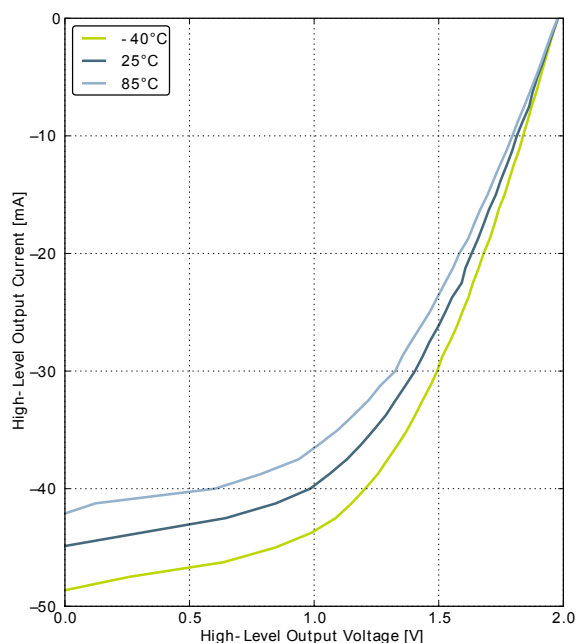
GPIO_Px_CTRL DRIVEMODE = LOWEST



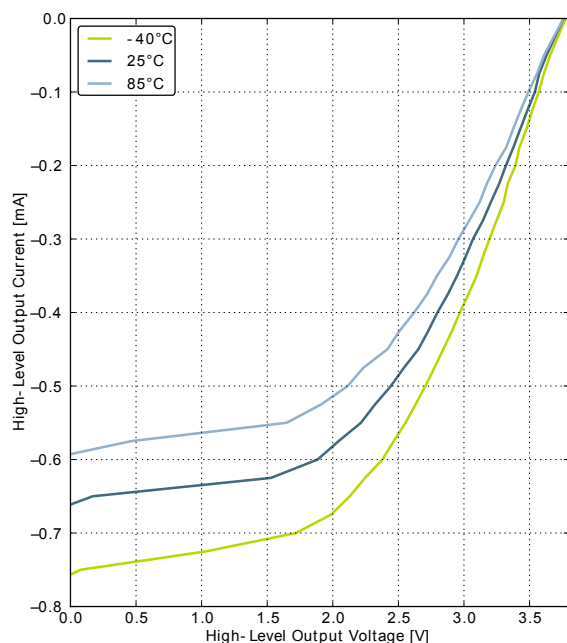
GPIO_Px_CTRL DRIVEMODE = LOW



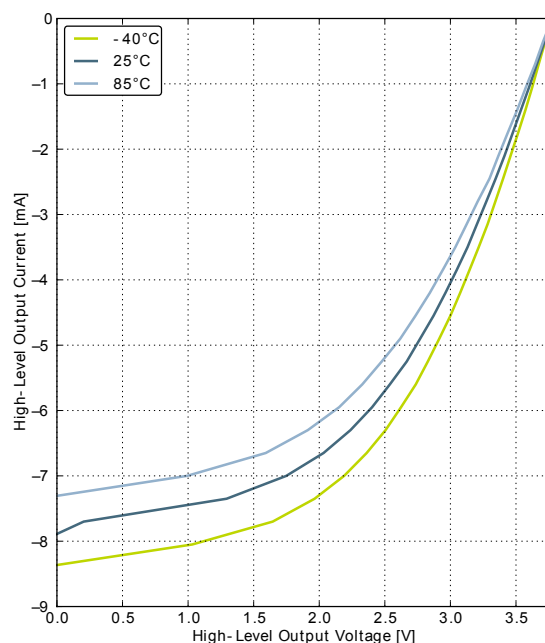
GPIO_Px_CTRL DRIVEMODE = STANDARD



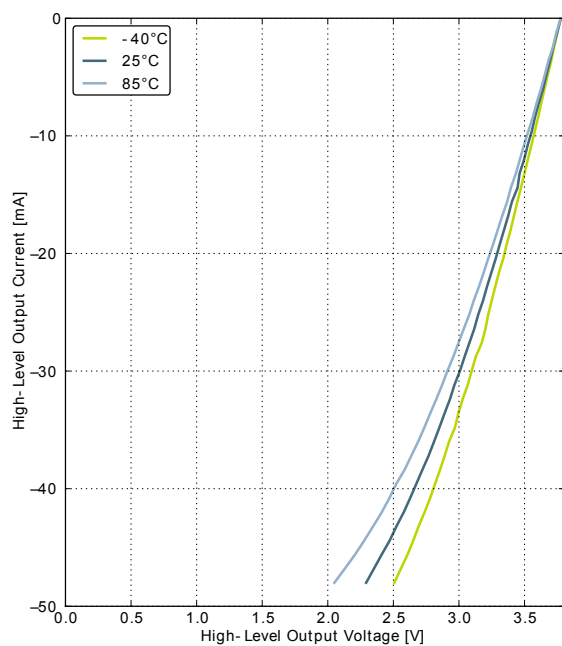
GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.19. Typical High-Level Output Current, 3.8V Supply Voltage

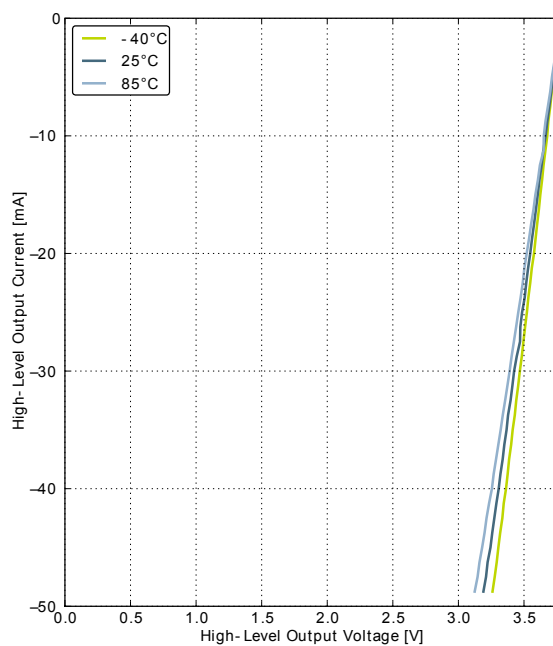
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

3.9.3 LFRCO

Table 3.10. LFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$		31.3	32.768	34.3	kHz
t_{LFRCO}	Startup time not including software calibration			150		μs
I_{LFRCO}	Current consumption			361	492	nA
TUNESTEP _{LFRCO}	Frequency step for LSB change in TUNING value			202		Hz

Figure 3.20. Calibrated LFRCO Frequency vs Temperature and Supply Voltage

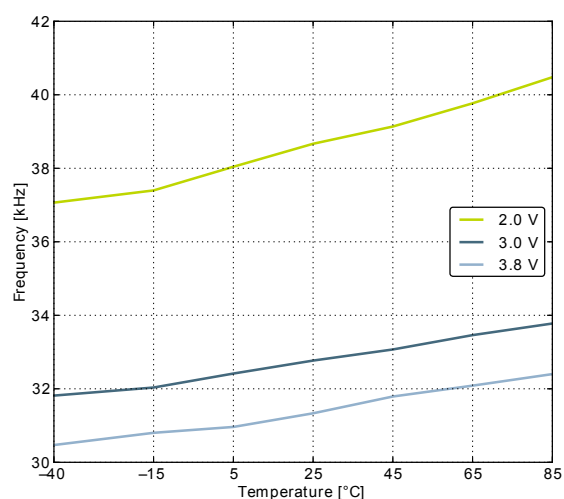
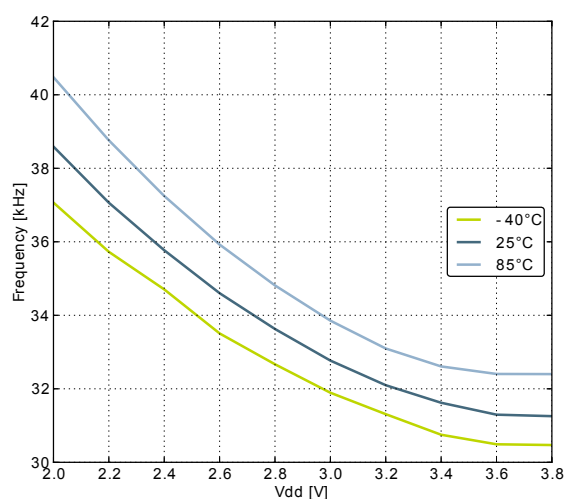


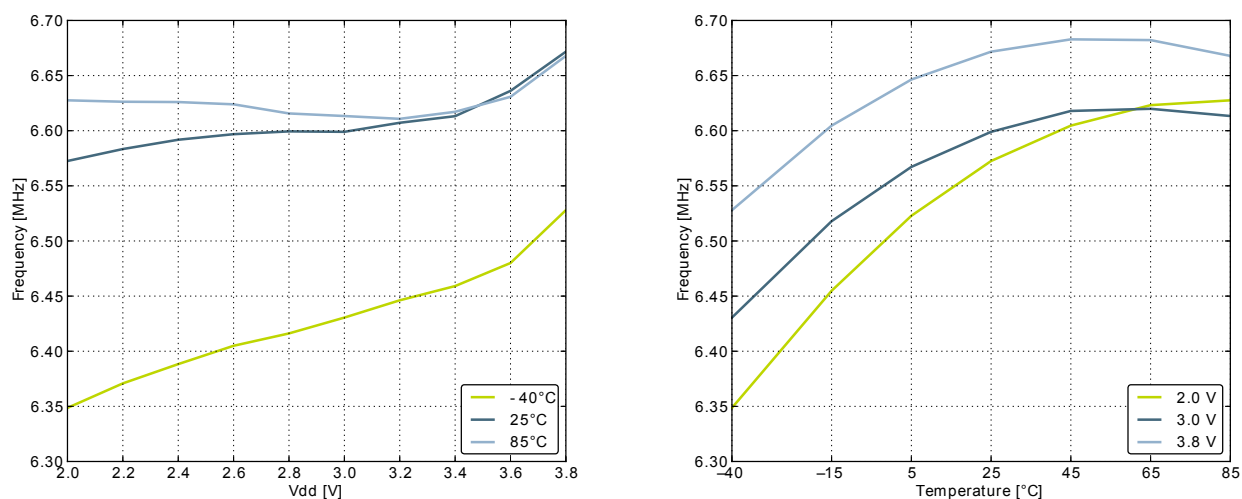
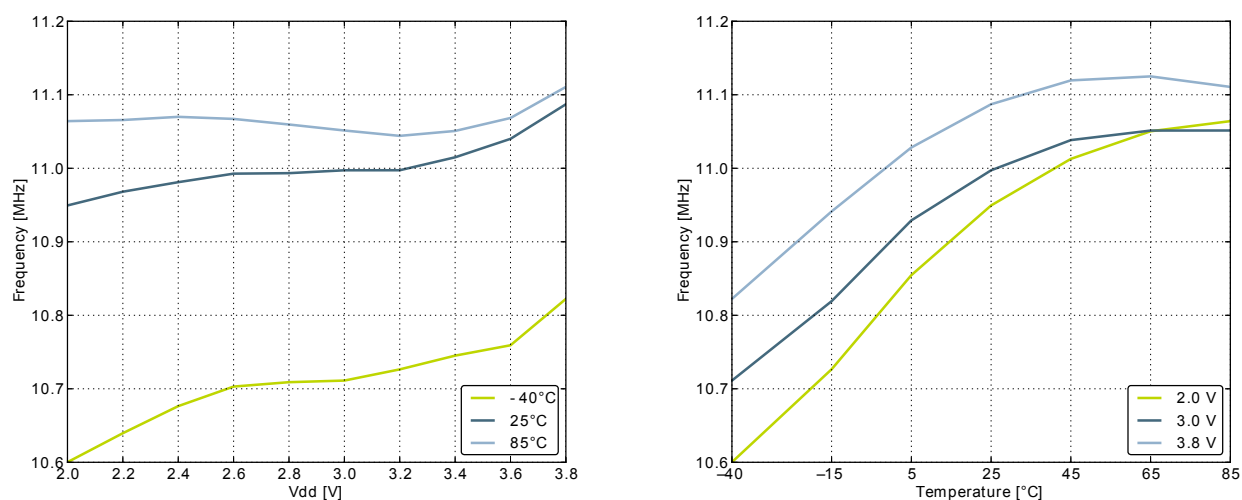
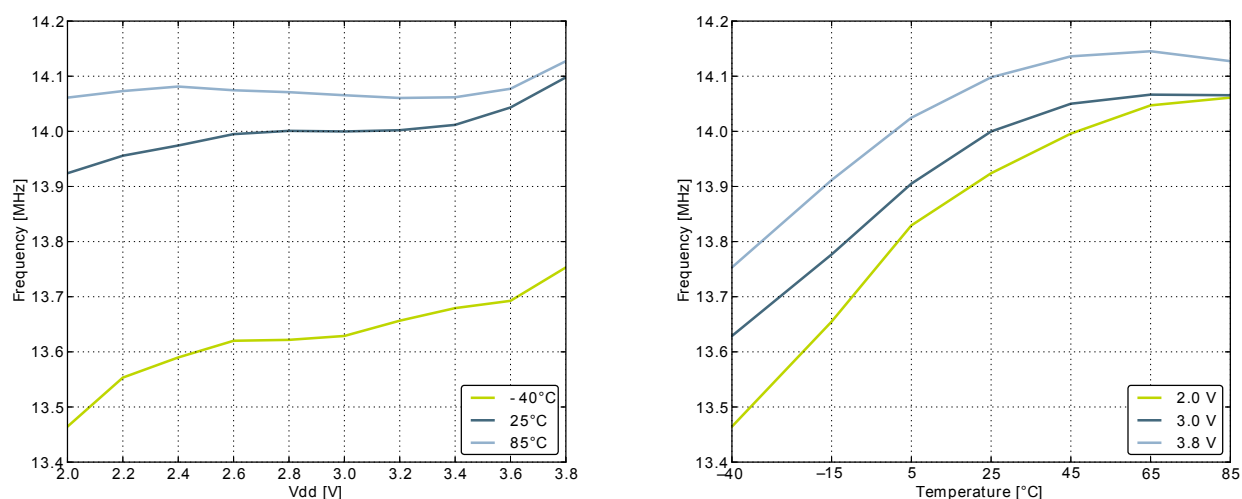
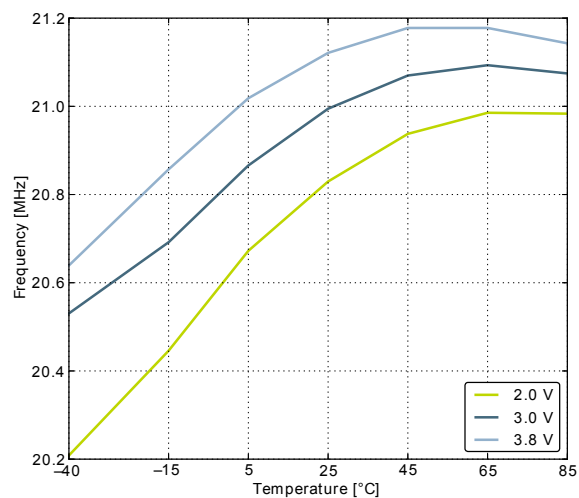
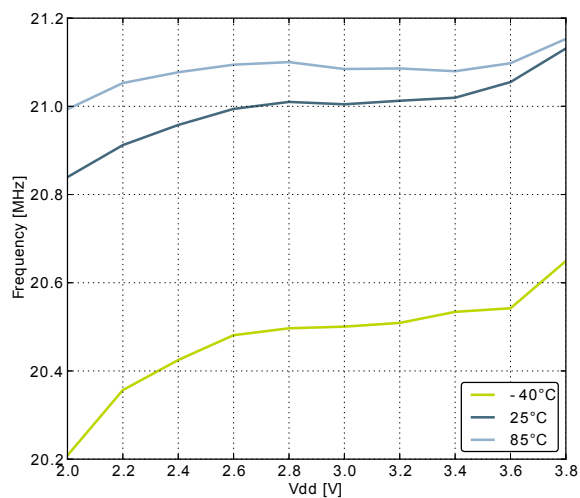
Figure 3.22. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature**Figure 3.23. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature****Figure 3.24. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature**

Figure 3.25. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature

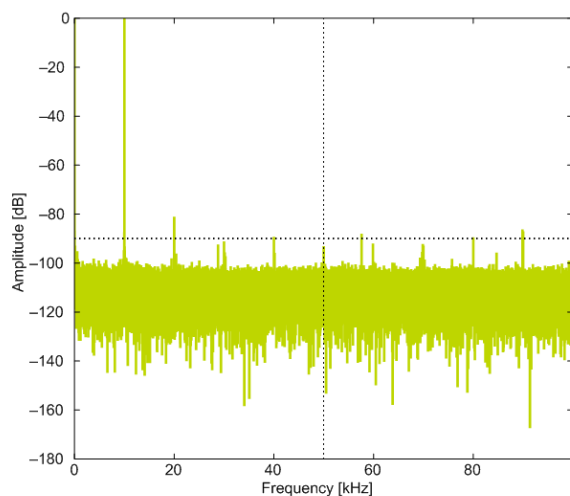
3.9.5 AUXHFRCO

Table 3.12. AUXHFRCO

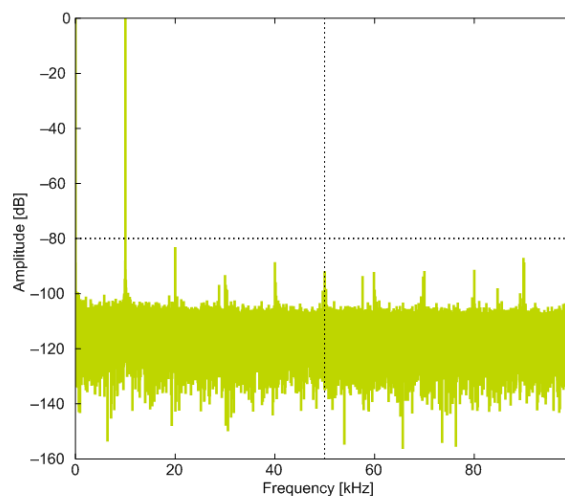
Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{AUXHFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$	21 MHz frequency band	20.37	21.0	21.63	MHz
		14 MHz frequency band	13.58	14.0	14.42	MHz
		11 MHz frequency band	10.67	11.0	11.33	MHz
		7 MHz frequency band	6.40	6.60	6.80	MHz
		1 MHz frequency band	1.15	1.20	1.25	MHz
$t_{\text{AUXHFRCO_settling}}$	Settling time after start-up	$f_{\text{AUXHFRCO}} = 14 \text{ MHz}$		0.6		Cycles
$\text{TUNESTEP}_{\text{AUXHFRCO}}$	Frequency step for LSB change in TUNING value	21 MHz frequency band		52.8		kHz
		14 MHz frequency band		36.9		kHz
		11 MHz frequency band		30.1		kHz
		7 MHz frequency band		18.0		kHz
		1 MHz frequency band		3.4		kHz

3.10.1 Typical performance

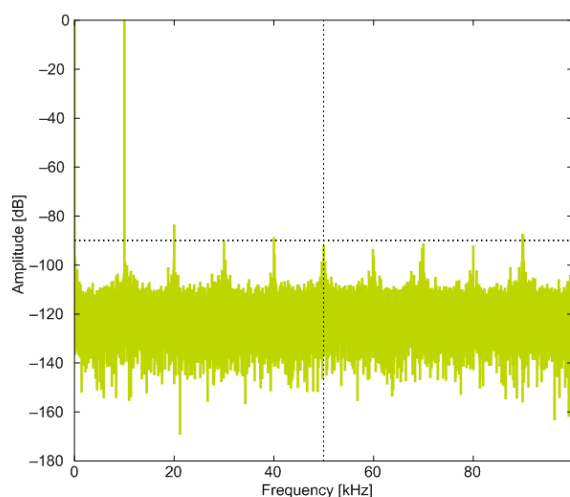
Figure 3.28. ADC Frequency Spectrum, $V_{dd} = 3V$, Temp = 25°C



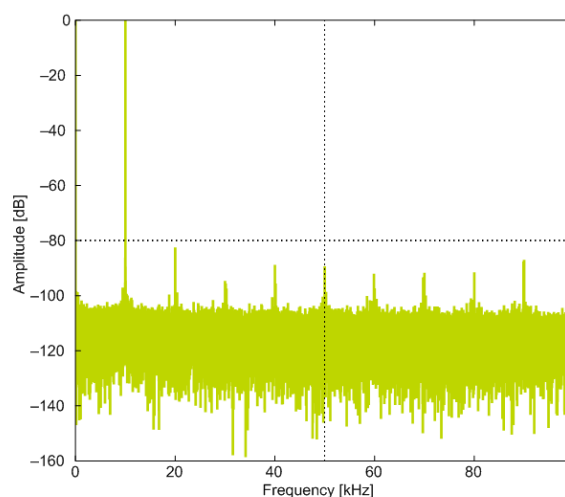
1.25V Reference



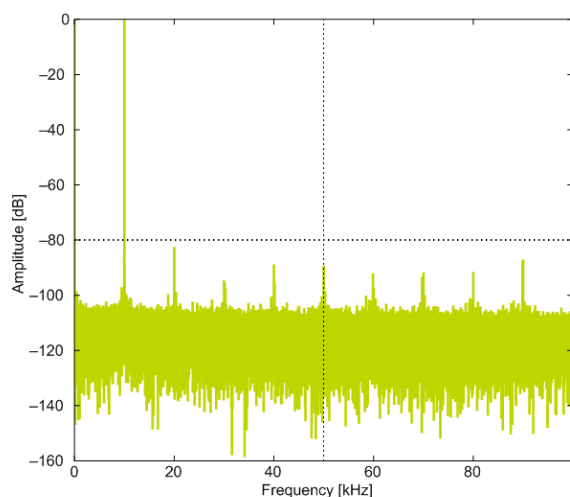
2.5V Reference



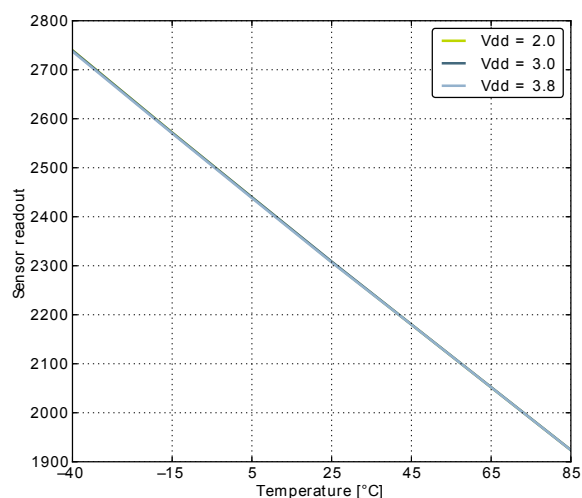
2XVDDVSS Reference



5VDIFF Reference



VDD Reference

Figure 3.33. ADC Temperature sensor readout

3.11 Current Digital Analog Converter (IDAC)

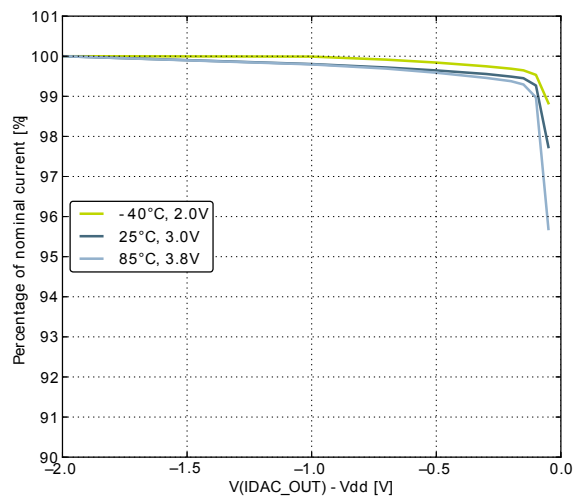
Table 3.16. IDAC Range 0 Source

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		13.0		μA
		Duty-cycled		10		nA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			0.85		μA
I_{STEP}	Step size			0.05		μA
I_D	Current drop at high impedance load	$V_{IDAC_OUT} = V_{DD} - 100mV$		0.79		%
TC_{IDAC}	Temperature coefficient	$V_{DD} = 3.0V$, STEPSEL=0x10		0.3		nA/°C
VC_{IDAC}	Voltage coefficient	$T = 25\text{ }^{\circ}C$, STEPSEL=0x10		11.7		nA/V

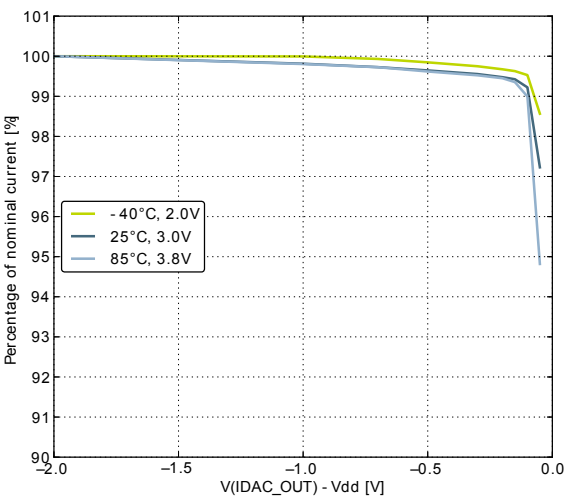
Table 3.17. IDAC Range 0 Sink

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{IDAC}	Active current with STEPSEL=0x10	EM0, default settings		15.1		μA
I_{0x10}	Nominal IDAC output current with STEPSEL=0x10			0.85		μA
I_{STEP}	Step size			0.05		μA
I_D	Current drop at high impedance load	$V_{IDAC_OUT} = 200\text{ mV}$		0.30		%
TC_{IDAC}	Temperature coefficient	$V_{DD} = 3.0\text{ V}$, STEPSEL=0x10		0.2		nA/°C
VC_{IDAC}	Voltage coefficient	$T = 25\text{ }^{\circ}C$, STEPSEL=0x10		12.5		nA/V

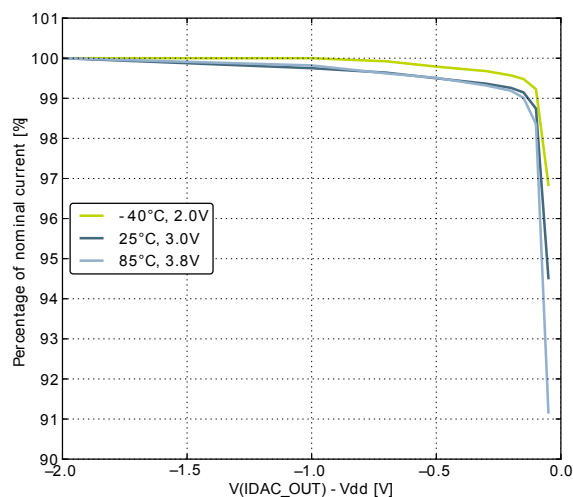
Figure 3.34. IDAC Source Current as a function of voltage on IDAC_OUT



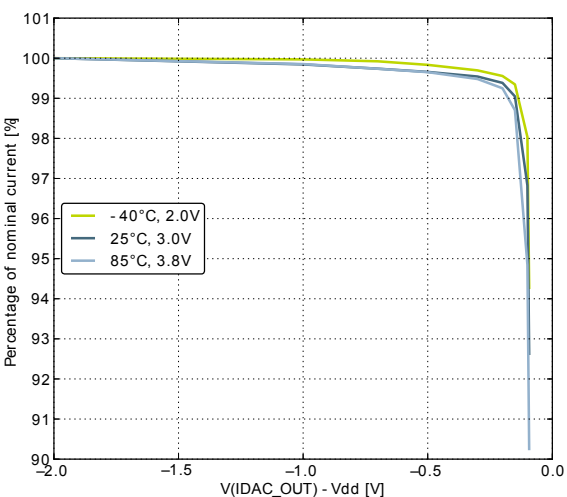
Range 0



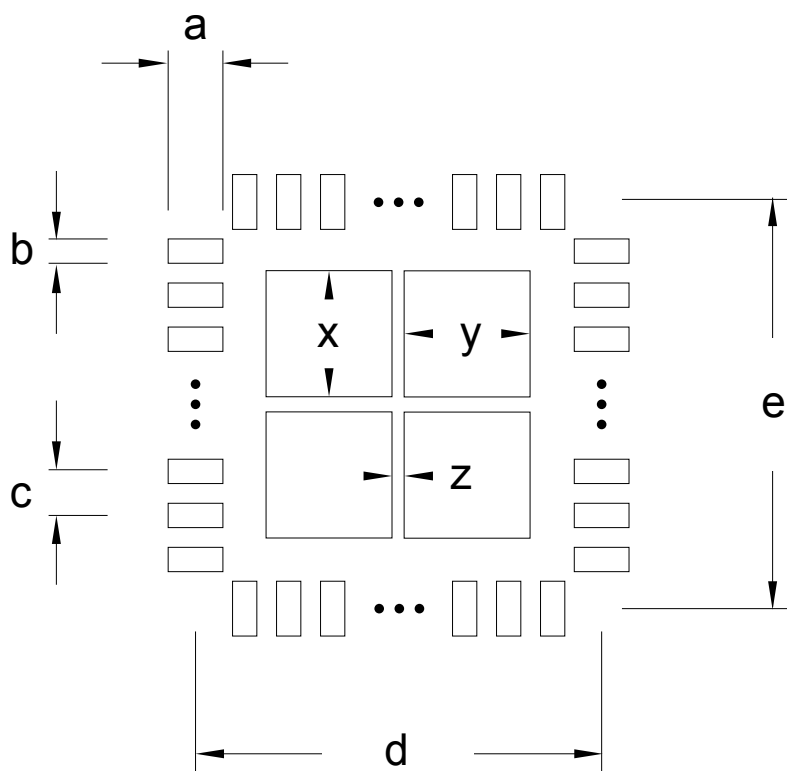
Range 1



Range 2



Range 3

Figure 5.3. QFN24 PCB Stencil Design**Table 5.3. QFN24 PCB Stencil Design Dimensions (Dimensions in mm)**

Symbol	Dim. (mm)	Symbol	Dim. (mm)
a	0.60	e	5.00
b	0.25	x	1.00
c	0.65	y	1.00
d	5.00	z	0.50

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.2 (p. 56) .

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

Place as many and as small as possible vias underneath each of the solder patches under the ground pad.

7 Revision History

7.1 Revision 1.00

December 4th, 2015

Updated all specs with results of full characterization.

Updated part number to revision B.

7.2 Revision 0.91

May 6th, 2015

Updated current consumption table for energy modes.

Updated GPIO max leakage current.

Updated startup time for HFXO and LFXO.

Updated current consumption for HFRCO and LFRCO.

Updated ADC current consumption.

Updated IDAC characteristics tables.

Updated ACMP internal resistance.

Updated VCMP current consumption.

7.3 Revision 0.90

March 16th, 2015

Note

This datasheet revision applies to a product under development. It's characteristics and specifications are subject to change without notice.

Corrected EM2 current consumption condition in Electrical Characteristics section.

Updated GPIO electrical characteristics.

Updated Max ESR_{HFXO} value for Crystal Frequency of 25 MHz.

Updated LFRCO plots.

Updated HFRCO table and plots.

Updated ADC table and temp sensor plot.

Added DMA current in Digital Peripherals section.

Updated block diagram.

Updated Package dimensions table.

Corrected leadframe type to matte-Sn.

7.4 Revision 0.20

December 11th, 2014

Preliminary Release.